

*ESD TR5.5-03-14*

# *ESD Association Technical Report*

*ESD TR5.5-03-14*

*For Electrostatic Discharge  
Sensitivity Testing –*

*Very-Fast Transmission Line  
Pulse (VF-TLP) –  
Round Robin Analysis*

*Authors:*

**Working Group 5.5,  
Transmission Line Pulse  
ESD Association**



*Electrostatic Discharge Association  
7900 Turin Road, Bldg. 3  
Rome, NY 13440*

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Published by:

**Electrostatic Discharge Association  
7900 Turin Road, Bldg. 3  
Rome, NY 13440**

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Printed in the United States of America

(This foreword is not part of ESD Association Technical Report ESD TR5.5-03-14)

**FOREWORD**

The ESD Association's working group 5.5 subcommittee conducted a round robin study to determine if the current VF-TLP standard practice (SP) yielded test results which would allow the elevation of the SP, with suitable modifications to a standard test method (STM). This technical report (TR) covers both the data taken and the analysis methods used to develop a precision statement for VF-TLP. This study involves seven test sites with eleven different test structures evaluated at each site. This paper summarizes these findings.

At the time ESD TR5.5-03-14 was prepared, the 5.5 (TLP) Device Testing Subcommittee had the following members:

	Theo Smedes, Chair NXP Semiconductors	
Robert Ashton ON Semiconductor	Jon Barth Barth Electronics, Inc.	Lorenzo Cerati STMicroelectronics
Marcel Dekker MASER Engineering	Reinhold Gaertner Infineon Technologies AG	Horst Gieser Fraunhofer EMFT
Vaughn Gross Green Mountain ESD Labs, Inc.	Evan Grund Grund Technical Solutions, LLC	Leo G. Henry ESDTLP Consultants
Timothy Maloney Intel Corporation	Thomas Meuse Thermo Fisher Scientific	Paul Phillips Phasix ESD
Bill Reynolds IBM	Alan Righter Analog Devices	Masanori Sawada HANWA Electronic Ind. Co., Ltd.
Wolfgang Stadler Intel Mobile Communications	Steven H. Voldman Steven H. Voldman LLC	Scott Ward Texas Instruments
	Terry Welsher, TAS Rep Dangelmayer Associates	

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The following individuals contributed significantly to the development of ESD TR5.5-03-14:

Detlef Bonfert  
Fraunhofer EMFT

Aniket Breed  
Intel

Tilo Brodbeck  
Infineon

Michael Chaine  
Micron Technology, Inc.

Charvaka Duvvury  
ESD Consulting, LLC

Michael Hopkins  
Hopkins Technical

Justin Katz  
Grund Technical Solutions,  
LLC

Mark Kelly  
Delphi Electronics

Kathleen Muhonen  
RF Micro Devices

Ravindra Narayan  
LSI

Nathaniel Peachey  
RF Micro Devices

Timothy Prass  
Raytheon

Karen Shrier  
Electronic Polymers

Larry Ting  
Texas Instruments

Roger Watkins  
Grund Technical Solutions,  
LLC

Heinrich Wolf  
Fraunhofer EMFT

Eugene Worley  
Qualcomm

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